



TO-126 Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)

Collector current

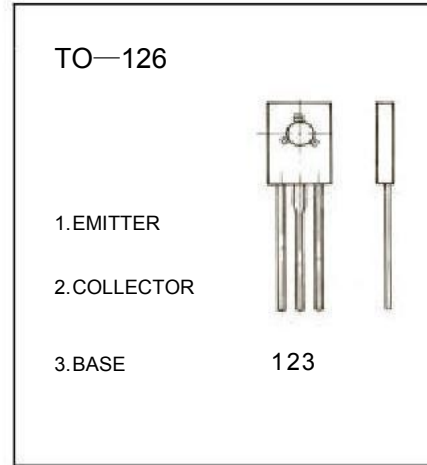
I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30V, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$			1	μA
DC current gain(note)	H_{FE}	$V_{CE}=2V, I_C=1A$	60		400	
DC current gain(note)	H_{FE}	$V_{CE}=2V, I_C=100mA$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=0.2A$			0.5	V
Base-emitter voltage	V_{BE}	$I_C=2A, I_B=0.2A$			1.5	V
Transition frequency	f_r	$V_{CE}=5V, I_C=0.1A$ $f=10MHz$	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-123	100-200	160-320	200-400

